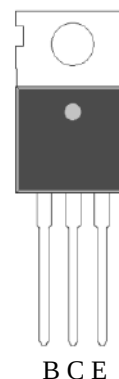


NPN Epitaxial Planar Transistor

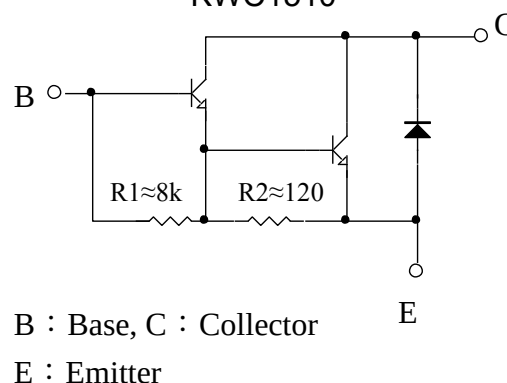
Features:

- High BV_{CEO}
- Low $V_{CE(SAT)}$
- High current gain
- Monolithic construction with built-in base-emitter shunt resistors
- Pb-free lead plating package

TO-220



KWC1510



Description

The KWC1510 is a NPN Darlington transistor, designed for general purpose amplifier and low speed switching application.

Ordering Information

Device	Package	Shipping
KWC1510	TO-220 (RoHS compliant package)	50pcs/tube, 20 tubes/box, 5 boxes / carton

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _{C(DC)}	10	A
	I _{C(Pulse)}	15 *1	
Power Dissipation	Pd(T _A =25°C)	2	W
	Pd(T _C =25°C)	65	
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : *1. Single Pulse P_w=100ms

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	150	-	-	V	I _C =100μA, I _E =0
BV _{CEO}	150	-	-	V	I _C =1mA, I _B =0
I _{CEO}	-	-	200	μA	V _{CE} =150V, I _E =0
I _{CBO}	-	-	200	μA	V _{CB} =150V, I _E =0
I _{EBO}	-	-	2	mA	V _{EB} =5V, I _C =0
*V _{CE(sat)} 1	-	-	1.5	V	I _C =5A, I _B =10mA
*V _{CE(sat)} 2	-	-	3	V	I _C =10A, I _B =100mA
*V _{CE(sat)} 3	-	-	2	V	I _C =5A, I _B =2.5mA
*V _{BE(sat)}	-	-	2	V	I _C =5A, I _B =5mA
*V _{BE(on)} 1	-	-	2.8	V	V _{CE} =3V, I _C =5A
*V _{BE(on)} 2	-	-	4.5	V	V _{CE} =3V, I _C =10A
*V _{FEC}	-	-	4	V	I _C =5A
*h _{FE} 1	2	-	20	K	V _{CE} =3V, I _C =5A
*h _{FE} 2	100	-	-	-	V _{CE} =3V, I _C =10A

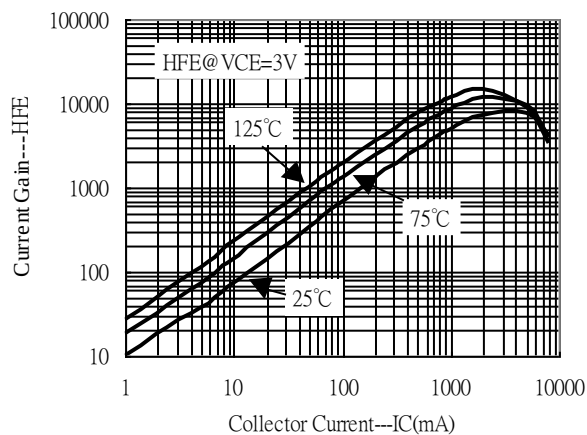
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of V_{CE(sat)} 1

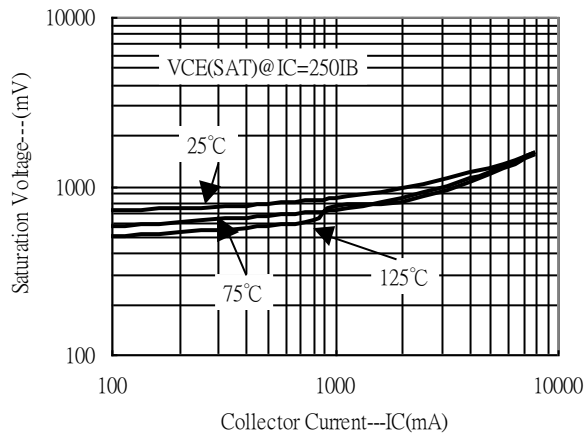
Rank	KA	N
Range	<1.1V	<1.5V

Typical Characteristics

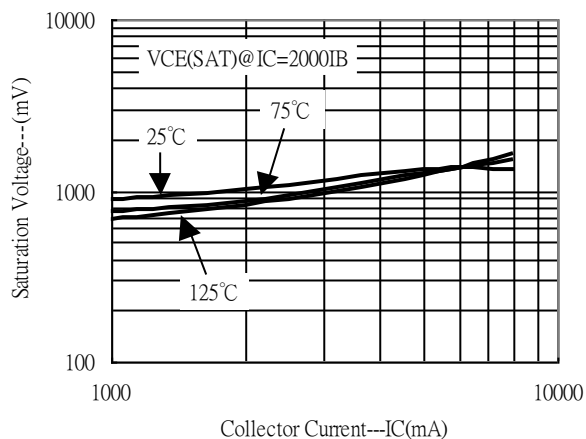
Current Gain vs Collector Current



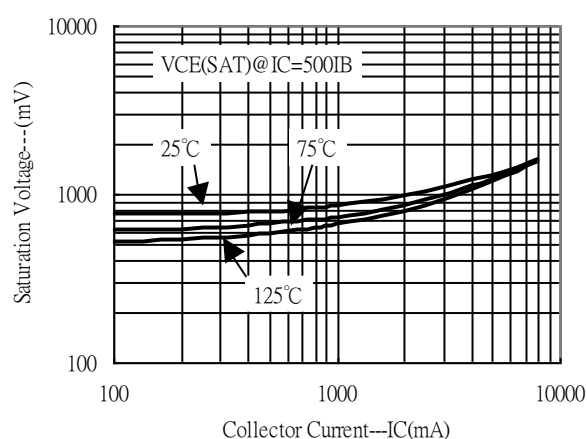
Saturation Voltage vs Collector Current



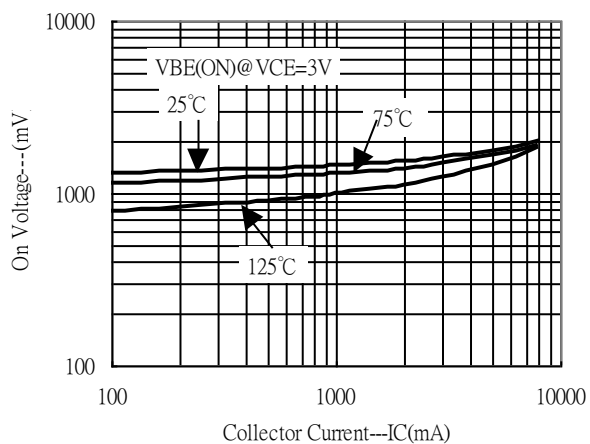
Saturation Voltage vs Collector Current



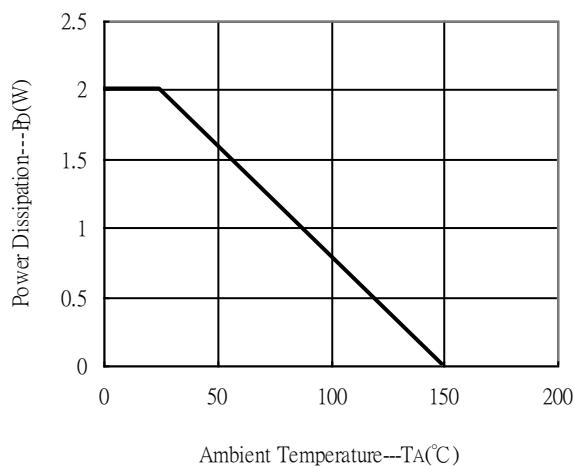
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current

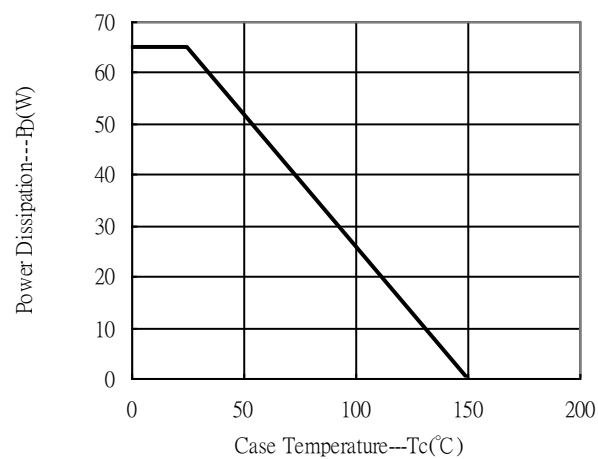


Power Derating Curve

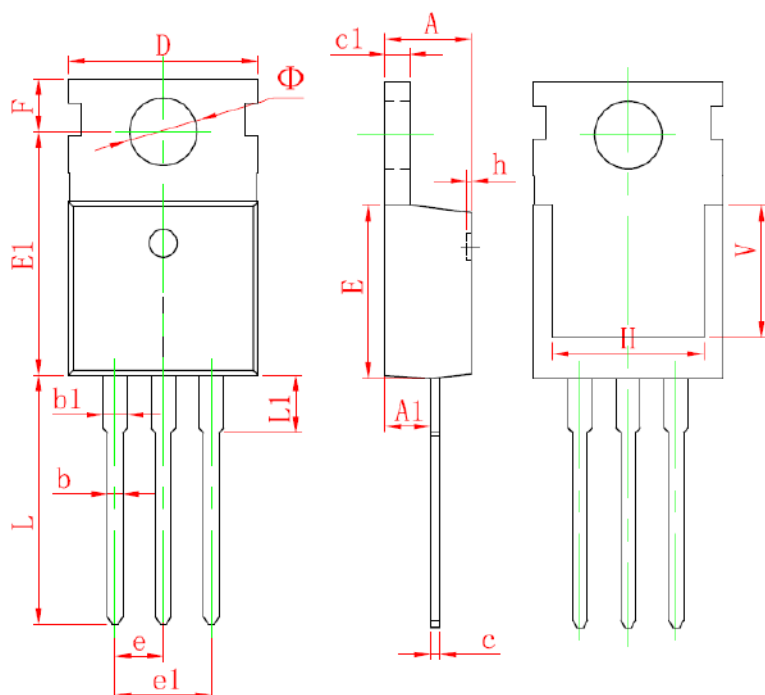


Typical Characteristics (Cont.)

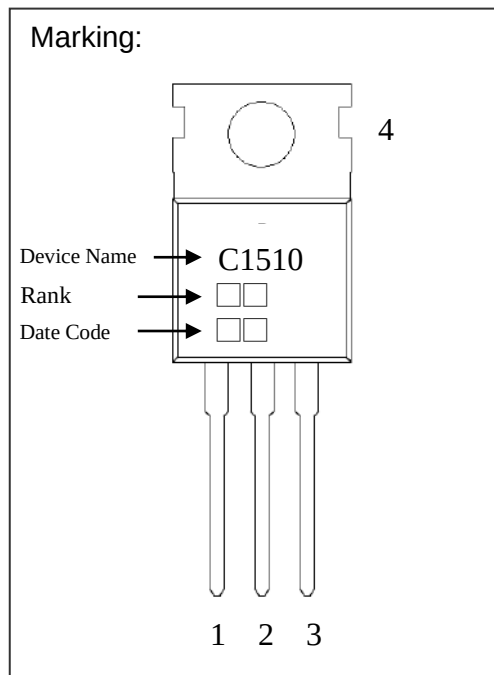
Power Derating Curve



TO-220 Dimension



3-Lead TO-220 Plastic Package



Style: Pin 1.Base 2.Collector 3.Emitter
 4.Collector

*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181	e	2.540*		0.100*	
A1	2.250	2.550	0.089	0.100	e1	4.980	5.180	0.196	0.204
b	0.710	0.910	0.028	0.036	F	2.650	2.950	0.104	0.116
b1	1.170	1.370	0.046	0.054	H	7.900	8.100	0.311	0.319
c	0.330	0.650	0.013	0.026	h	0.000	0.300	0.000	0.012
c1	1.200	1.400	0.047	0.055	L	12.900	13.400	0.508	0.528
D	9.910	10.250	0.390	0.404	L1	2.850	3.250	0.112	0.128
E	8.950	9.750	0.352	0.384	V	7.500	REF	0.295	REF
E1	12.650	12.950	0.498	0.510	Φ	3.400	3.800	0.134	0.150